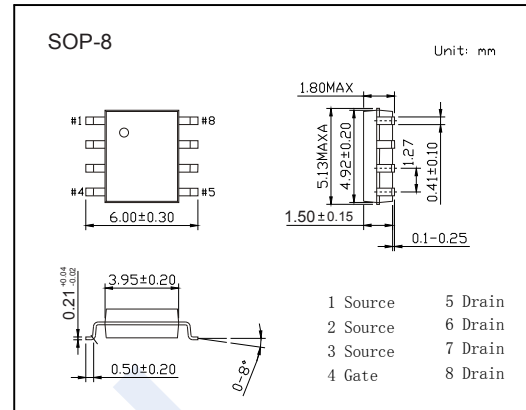
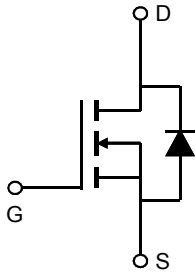


N-Channel MOSFET

AO4476A (KO4476A)

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 15 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 7.7m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 10.8m\Omega (V_{GS} = 4.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_A=25^\circ C$	15
		$T_A=70^\circ C$	12
Pulsed Drain Current	I_{DM}	110	A
Avalanche Current	I_{AS}, I_{AR}	27	
Avalanche Energy	$L=0.1mH$	E_{AS}, E_{AR}	36
Power Dissipation	P_D	$T_A=25^\circ C$	3.1
		$T_A=70^\circ C$	2
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	40
		Steady-State	75
Thermal Resistance.Junction- to-Lead	R_{thJL}	24	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

N-Channel MOSFET

AO4476A (KO4476A)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250μA, V _{GS} =0V	30			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA	
		V _{DS} =30V, V _{GS} =0V, T _J =55°C			5		
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.5		2.5	V	
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =15A			7.7	mΩ	
		V _{GS} =10V, I _D =15A, T _J =125°C			12		
		V _{GS} =4.5V, I _D =12A			10.8		
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =5V	110			A	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =15A		45		S	
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz	920		1380	pF	
Output Capacitance	C _{oss}		125		235		
Reverse Transfer Capacitance	C _{rss}		60		150		
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.55		1.65	Ω	
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =15A	16		24	nC	
Total Gate Charge (4.5V)			7.6		11.4		
Gate Source Charge			Q _{gs}	2			3.2
Gate Drain Charge			Q _{gd}	3			7
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{DS} =15V, R _L =1Ω, R _{GEN} =3Ω		6.5		ns	
Turn-On Rise Time	t _r			2			
Turn-Off DelayTime	t _{d(off)}			17			
Turn-Off Fall Time	t _f			3.5			
Body Diode Reverse Recovery Time	t _{rr}	I _F = 15A, di/dt = 500A/μs	7		10.5	nC	
Body Diode Reverse Recovery Charge	Q _{rr}		11		16		
Maximum Body-Diode Continuous Current	I _S				4	A	
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V	

Note : The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	4476A KC****
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N-Channel MOSFET AO4476A (KO4476A)

■ Typical Characteristics

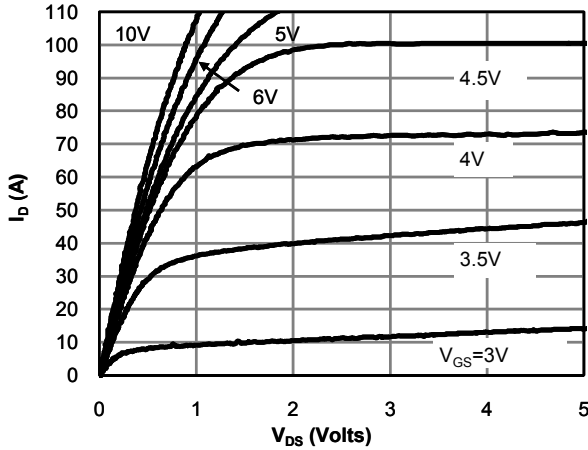


Figure 1: On-Region Characteristics (Note E)

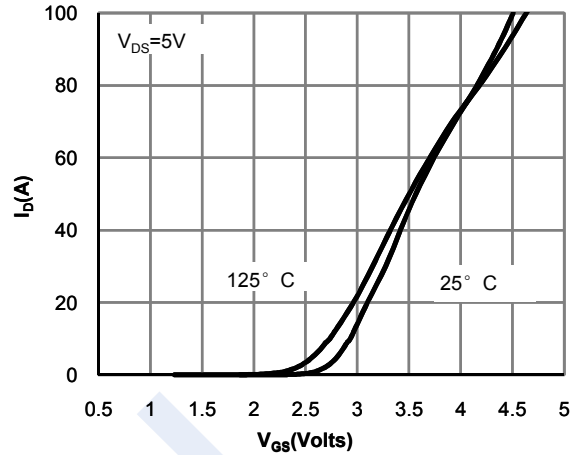


Figure 2: Transfer Characteristics (Note E)

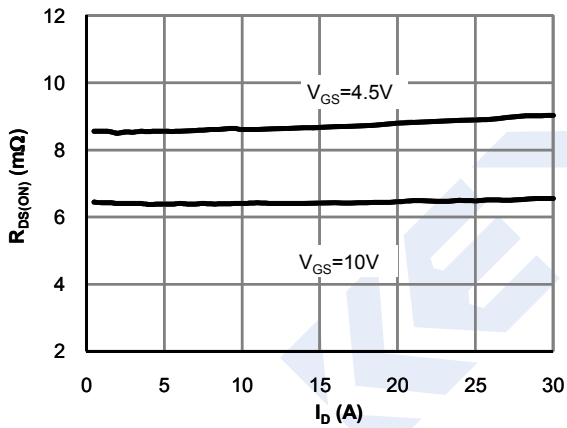


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

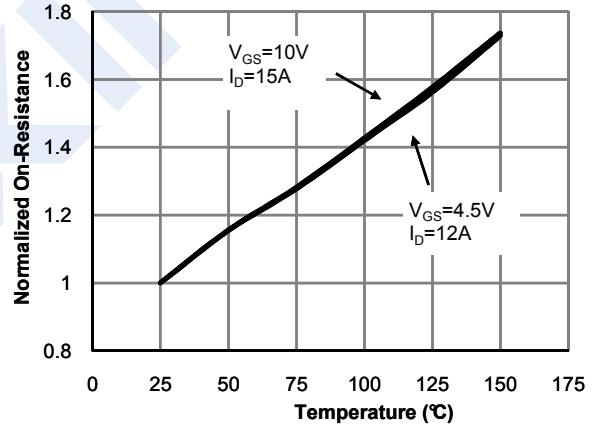


Figure 4: On-Resistance vs. Junction Temperature (Note E)

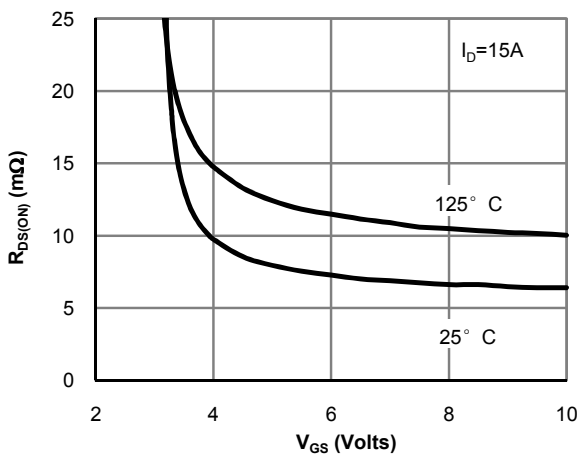


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

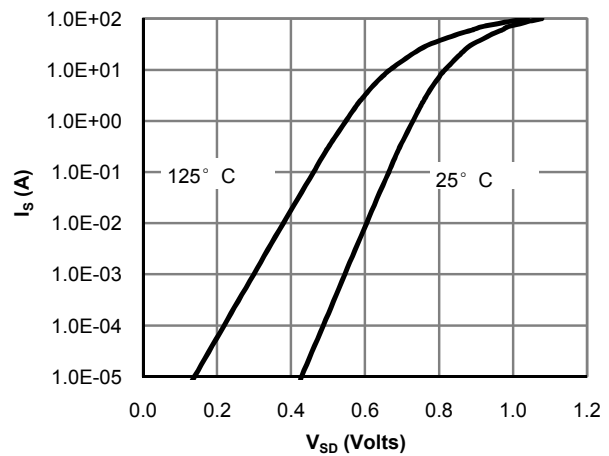


Figure 6: Body-Diode Characteristics (Note E)

N-Channel MOSFET AO4476A (KO4476A)

■ Typical Characteristics

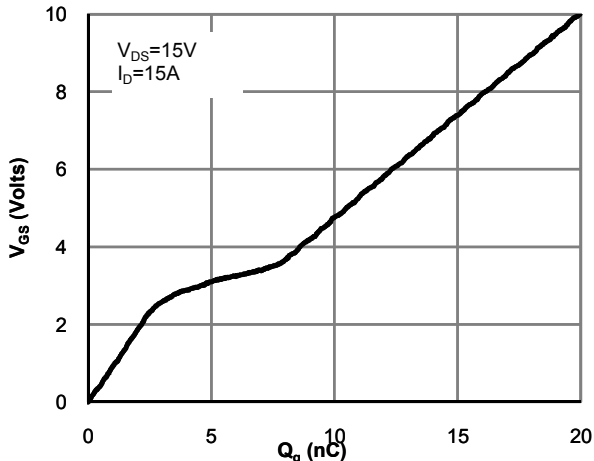


Figure 7: Gate-Charge Characteristics

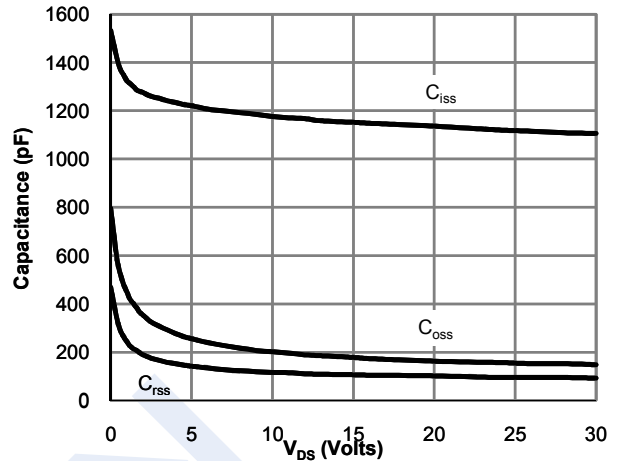


Figure 8: Capacitance Characteristics

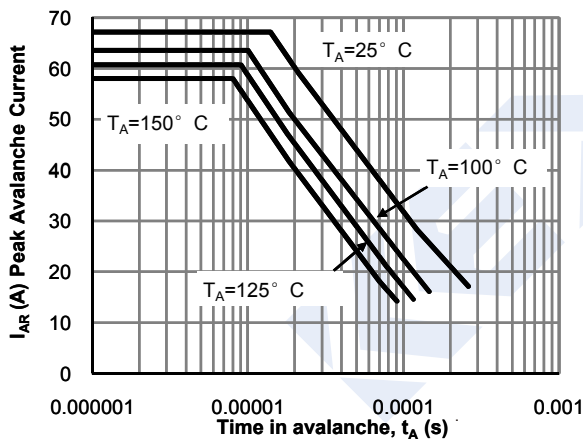


Figure 9: Single Pulse Avalanche capability (Note C)

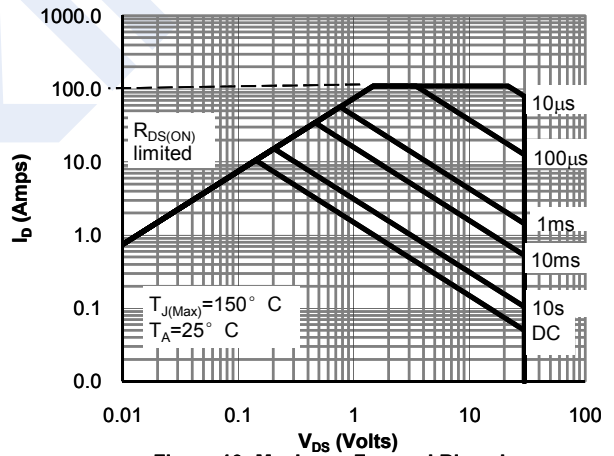


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

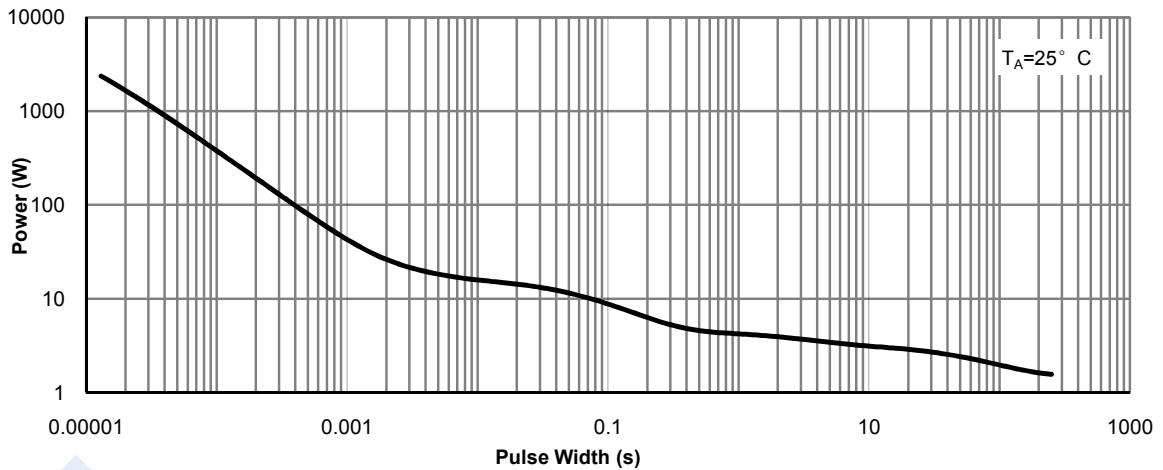


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

N-Channel MOSFET AO4476A (KO4476A)

■ Typical Characteristics

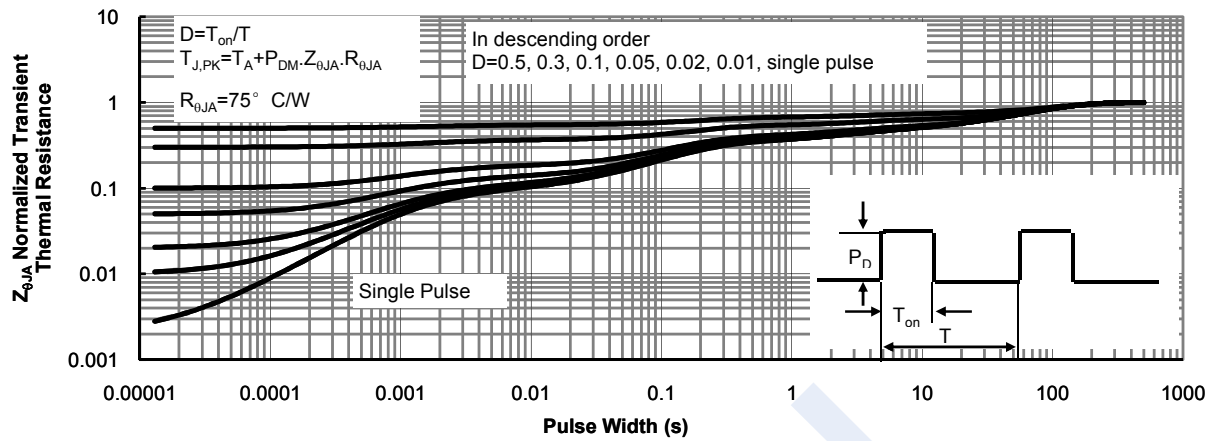


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)